

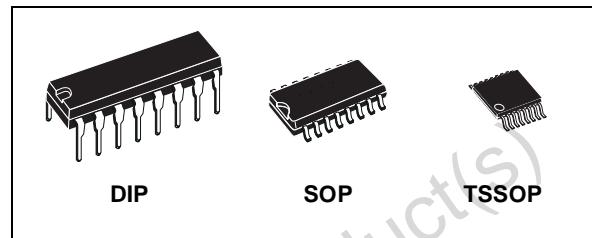
SINGLE 8-CHANNEL ANALOG MULTIPLEXER/DEMULITPLEXER

- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu A$ (MAX.) at $T_A=25^\circ C$
- LOGIC LEVEL TRANSLATION TO ENABLE TTL LOGIC SIGNAL TO COMMUNICATE WITH $\pm 5V$ ANALOG SIGNAL
- LOW "ON" RESISTANCE:
70 Ω TYP. ($V_{CC} - V_{EE} = 4.5V$)
50 Ω TYP. ($V_{CC} - V_{EE} = 9V$)
- WIDE ANALOG INPUT VOLTAGE RANGE:
 $\pm 6V$
- FAST SWITCHING:
 $t_{pd} = 13ns$ (TYP.) at $T_A = 25^\circ C$
- LOW CROSSTALK BETWEEN SWITCHES
- HIGH ON/OFF OUTPUT VOLTAGE RATIO
- WIDE OPERATING SUPPLY VOLTAGE RANGE ($V_{CC} - V_{EE}$) = 2V TO 12V
- LOW SINE WAVE DISTORTION:
0.02% at $V_{CC} - V_{EE} = 9V$
- COMPATIBLE WITH TTL OUTPUTS:
 $V_{IH} = 2V$ (MIN.) $V_{IL} = 0.8V$ (MAX.)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4051

DESCRIPTION

The M74HCT4051 is a single eight-channel analog MULTIPLEXER/DEMULITPLEXER fabricated with silicon gate C²MOS technology and it is pin to pin compatible with the equivalent metal gate CMOS4000B series.

It contains 8 bidirectional and digitally controlled analog switches.



ORDER CODES

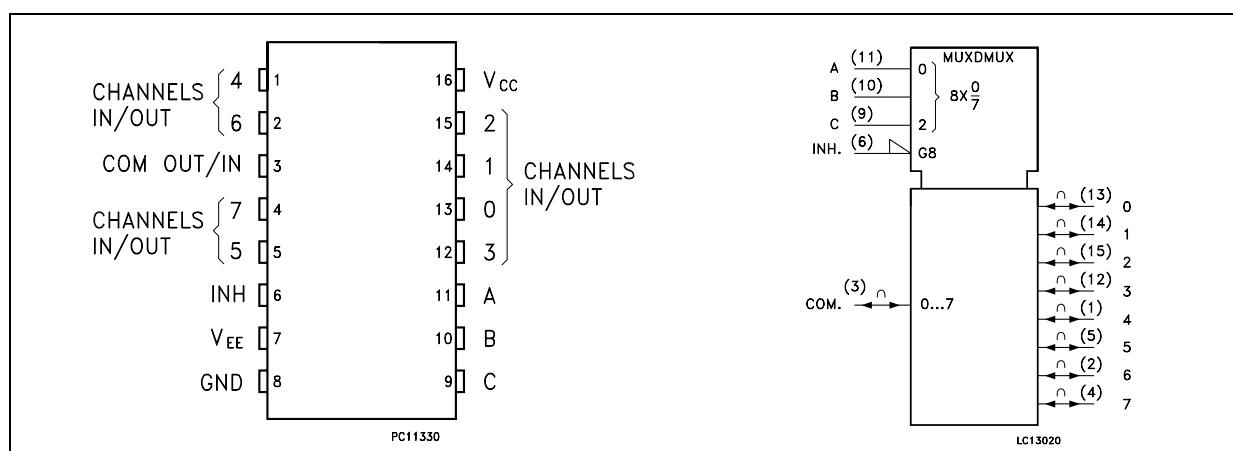
PACKAGE	TUBE	T & R
DIP	M74HCT4051B1R	
SOP	M74HCT4051M1R	M74HCT4051RM13TR
TSSOP		M74HCT4051TTR

A built-in level shifting is included to allow an input range up to $\pm 6V$ (peak) for an analog signal with digital control signal of 0 to 6V.

V_{EE} supply pin is provided for analog input signals. It has an inhibit (INH) input terminal to disable all the switches when high, compatible with TTL output level. For operation as a digital multiplexer/demultiplexer, VEE is connected to GND. A, B and C control inputs select one channel out of eight channels; they are compatible with TTL output level.

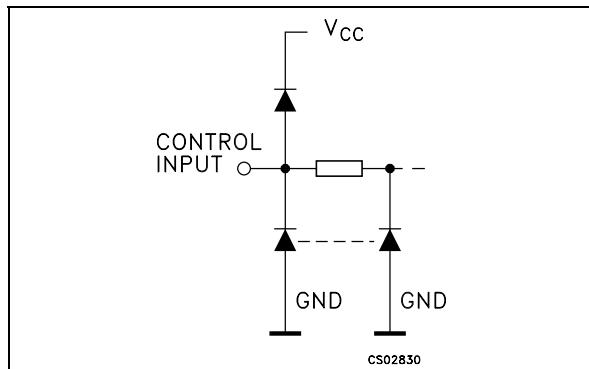
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



M74HCT4051

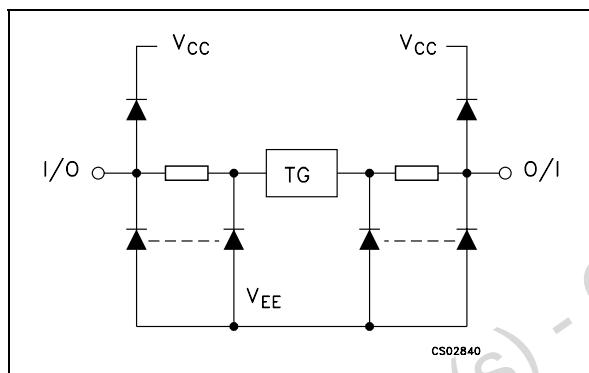
CONTROL INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
3	COM OUT/IN	Common Output/Input
6	INH	INHIBIT Input
7	V _{EE}	Negative Supply Voltage
11, 10, 9	A, B, C	Select Inputs
13, 14, 15, 12, 1, 5, 2, 4	0 to 7	Independent Input/Outputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

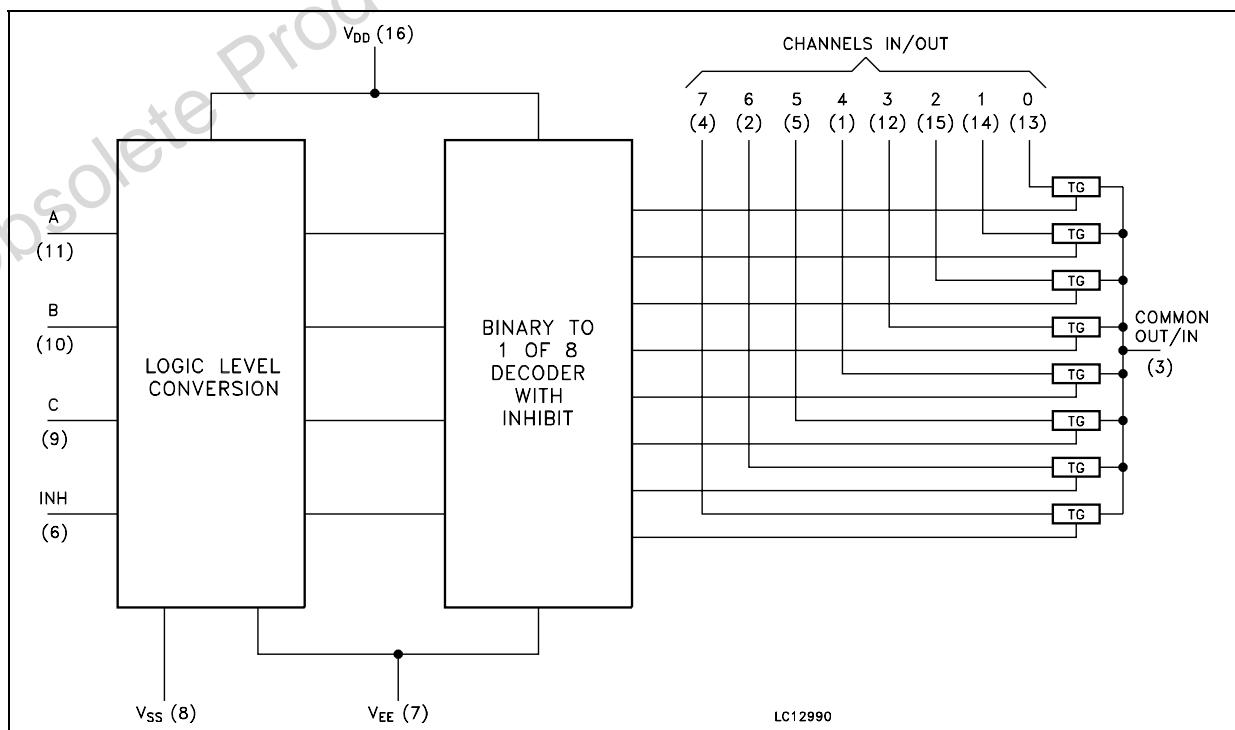
I/O EQUIVALENT CIRCUIT



TRUTH TABLE

INPUT STATE				ON CHANNEL
INH	C	B	A	
L	L	L	L	0
L	L	L	H	1
L	L	H	L	2
L	L	H	H	3
L	H	L	L	4
L	H	L	H	5
L	H	H	L	6
L	H	H	H	7
H	X	X	X	NONE

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
$V_{CC} - V_{EE}$	Supply Voltage	-0.5 to +13	V
V_I	Control Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_{I/O}$	Switch I/O Voltage	$V_{EE} - 0.5$ to $V_{CC} + 0.5$	V
I_{CK}	Control Input Diode Current	± 20	mA
I_{IOK}	I/O Diode Current	± 20	mA
I_T	Switch Through Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_{EE}	Supply Voltage	-6 to 0	V
$V_{CC} - V_{EE}$	Supply Voltage	2 to 12	V
V_I	Input Voltage	0 to V_{CC}	V
$V_{I/O}$	I/O Voltage	V_{EE} to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 4.5$ to 5.5V	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition			Value						Unit	
		V_{CC} (V)	V_{EE} (V)		$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IHC}	High Level Input Voltage	4.5 to 5.5			2.0			2.0		2.0		V
V_{ILC}	Low Level Input Voltage	4.5 to 5.5					0.8		0.8		0.8	V
R_{ON}	ON Resistance	4.5	GND	$V_I = V_{IHC} \text{ or } V_{ILC}$ $V_{I/O} = V_{CC} \text{ to } V_{EE}$ $I_{I/O} \leq 2\text{mA}$		85	180		225		270	Ω
		4.5	-4.5			55	120		150		180	
		4.5	GND	$V_I = V_{IHC} \text{ or } V_{ILC}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} \leq 2\text{mA}$		70	150		190		230	
		4.5	-4.5			50	100		125		150	
ΔR_{ON}	Difference of ON Resistance between switches	4.5	GND	$V_I = V_{IHC} \text{ or } V_{ILC}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} \leq 2\text{mA}$		10	30		35		45	Ω
		4.5	-4.5			5	12		15		18	
I_{OFF}	Input/Output Leakage Current (SWITCH OFF)	5.5	GND	$V_{OS} = V_{CC} \text{ or GND}$ $V_{IS} = \text{GND or } V_{CC}$ $V_I = V_{ILC} \text{ or } V_{IHC}$			± 0.06		± 0.6		± 1.0	μA
		5.5	-6.0				± 0.1		± 1		± 1	
I_{IZ}	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	5.5	GND	$V_{OS} = V_{CC} \text{ or GND}$ $V_I = V_{IHC} \text{ or } V_{ILC}$			± 0.06		± 0.6		± 1.0	μA
		5.5	-6.0				± 0.1		± 1		± 1	
I_I	Input Leakage Current	5.5	GND	$V_I = V_{CC} \text{ or GND}$			± 0.1		± 0.1		± 1	μA
I_{CC}	Quiescent Supply Current	5.5	GND	$V_I = V_{CC} \text{ or GND}$			4		40		80	μA
		5.5	-6.0				8		80		160	
ΔI_{CC}	Additional Quiescent Supply Current per input pin	4.5 to 5.5	GND	$V_I = V_{CC} - 2.1V$ other input at V_{CC} or GND		100	360		450		490	μA

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6\text{ns}$)

Symbol	Parameter	Test Condition			Value						Unit	
		V_{CC} (V)	V_{EE} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		
$\Phi_{I/O}$	Phase Difference Between Input and Output	4.5	GND	$C_L = 50\text{pF}$		5	12		15		18	ns
		4.5	-4.5			4	8		10		12	
t_{PZL} t_{PZH}	Output Enable Time	4.5	GND	$R_L = 1\text{K}\Omega$ $C_L = 50\text{pF}$		13	45		56		68	ns
		4.5	-4.5			11	34		43		51	
t_{PLZ} t_{PHZ}	Output Disable Time	4.5	GND	$R_L = 1\text{K}\Omega$ $C_L = 50\text{pF}$		25	38		48		58	ns
		4.5	-4.5			19	31		39		47	

CAPACITANCE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value						Unit	
		V_{CC} (V)	V_{EE} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		
C_{IN}	Input Capacitance	5.0				5	10		10		10	pF
$C_{I/O}$	Common Terminal Capacitance	5.0	-5.0			11	20		20		20	pF
$C_{I/O}$	Switch Terminal Capacitance	5.0	-5.0			7	15		15		15	pF
C_{IOS}	Feed Through Capacitance	5.0	-5.0			0.75	2		2		2	pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0	GND			67						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

M74HCT4051

ANALOG SWITCH CHARACTERISTICS (GND = 0V; T_A = 25°C)

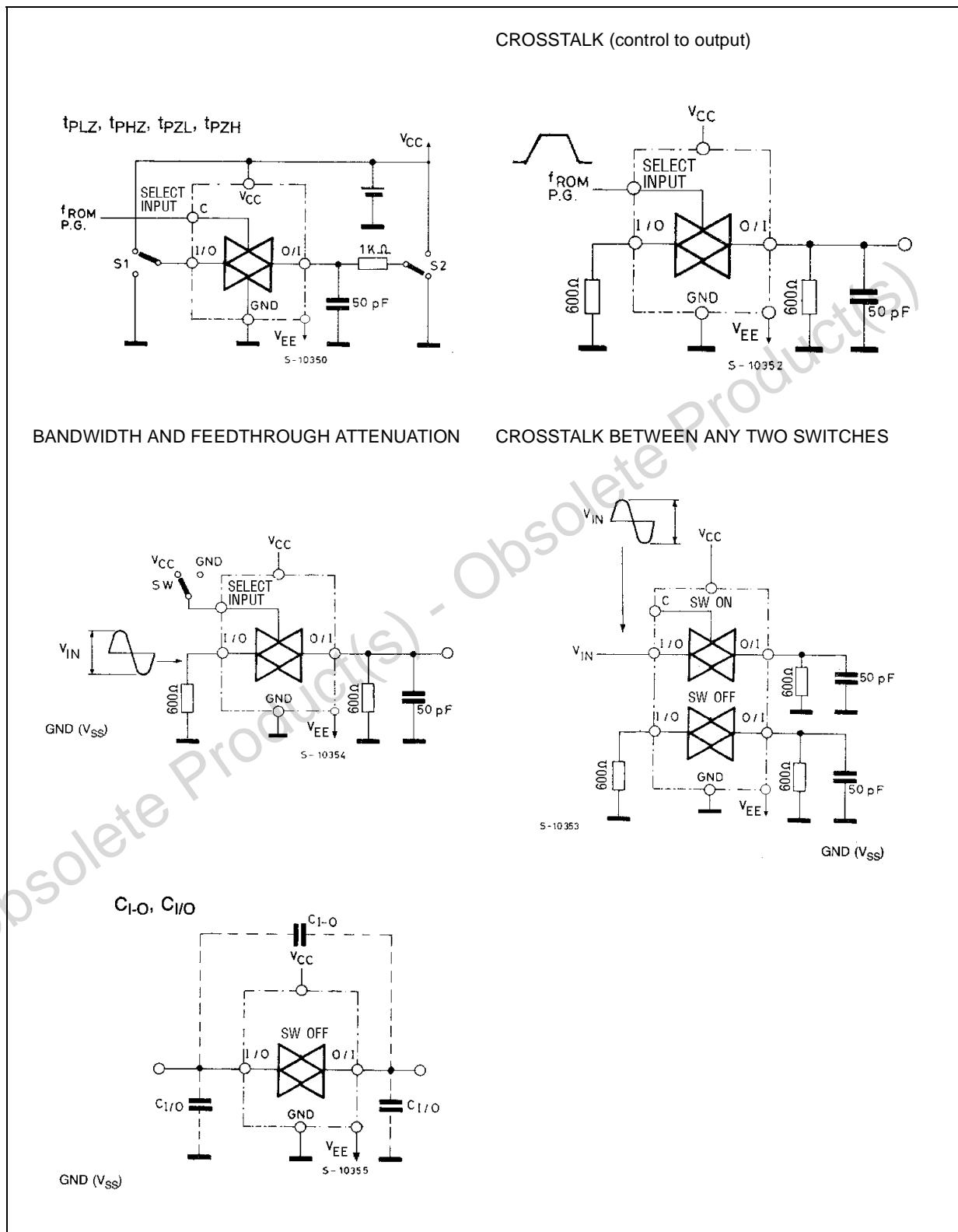
Symbol	Parameter	Test Condition				Value	Unit	
		V _{CC} (V)	V _{EE} (V)	V _{IN} (V _{p-p})		Typ.		
	Sine Wave Distortion	2.25	-2.25	4	$f_{IN} = 1 \text{ KHz}$ $R_L = 10 \text{ K}\Omega$, $C_L = 50 \text{ pF}$	0.025	%	
		4.5	-4.5	8		0.020		
	Sine Wave Distortion	2.25	-2.25	4	$f_{IN} = 10 \text{ KHz}$ $R_L = 10 \text{ K}\Omega$, $C_L = 50 \text{ pF}$	0.12	%	
		4.5	-4.5	8		0.06		
f _{MAX}	Frequency Response (Switch ON) (*)	2.25	-2.25	Adjust f _{IN} voltage to obtain 0 dBm at V _{OS} . Increase f _{IN} Frequency until dB meter reads -3dB $R_L = 50\Omega$, $C_L = 10 \text{ pF}$, $f_{IN} = 1\text{KHz}$ sine wave			MHz	
		4.5	-4.5					
f _{MAX}	Frequency Response (Switch ON) (**)	2.25	-2.25	Adjust f _{IN} voltage to obtain 0 dBm at V _{OS} . Increase f _{IN} Frequency until dB meter reads -3dB $R_L = 50\Omega$, $C_L = 10 \text{ pF}$, $f_{IN} = 1\text{KHz}$ sine wave			MHz	
		4.5	-4.5					
		6.0	-6.0					
	Feed through Attenuation (Switch OFF)	2.25	-2.25	V _{IN} is centered at $(V_{CC} - V_{EE})/2$ Adjust input for 0 dBm $R_L = 600\Omega$, $C_L = 50 \text{ pF}$, $f_{IN} = 1\text{MHz}$ sine wave			dB	
		4.5	-4.5					
	Crosstalk (Control Input to Signal Output)	4.5	0	Adjust R _L at set up so that I _S = 0A. $R_L = 600\Omega$, $C_L = 50 \text{ pF}$, $f_{IN} = 1\text{MHz}$ square wave between V _{cc} and GND tr=tf= 6 ns			mV	
		4.5	-4.5					
	Crosstalk (between any two switches)	2.25	-2.25	Adjust V _{IN} to obtain 0dBm at input $R_L = 600\Omega$, $C_L = 50 \text{ pF}$, $f_{IN} = 1\text{MHz}$ sine wave			dB	
		4.5	-4.5					

(*) Input COMMON Terminal, and measured at SWITCH Terminal

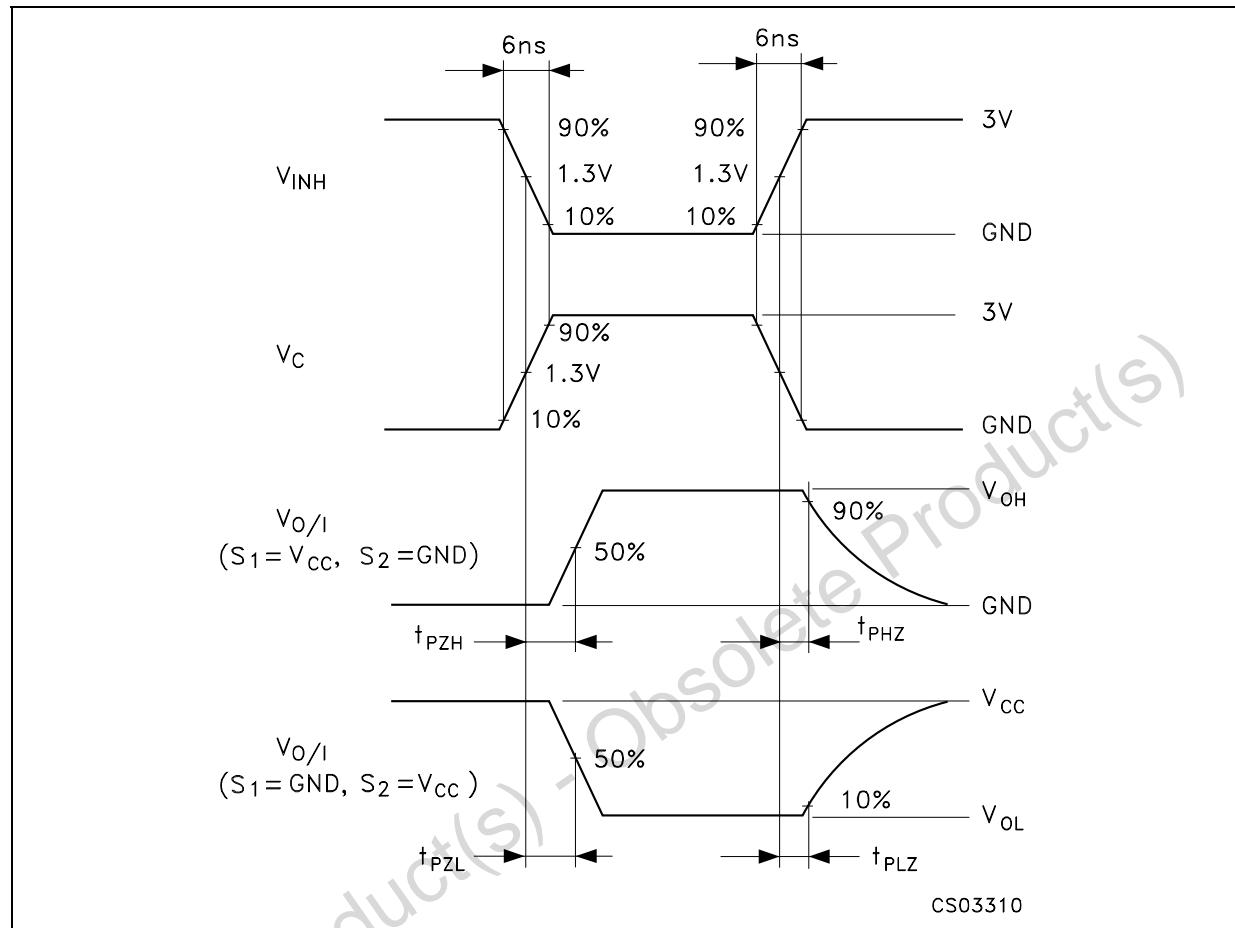
(**) Input SWITCH Terminal, and measured at common Terminal

NOTE: These characteristics are determined by the design of the device.

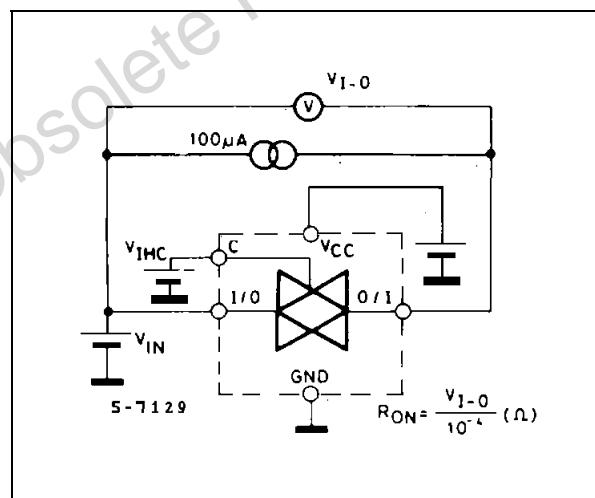
SWITCHING CHARACTERISTICS TEST CIRCUIT



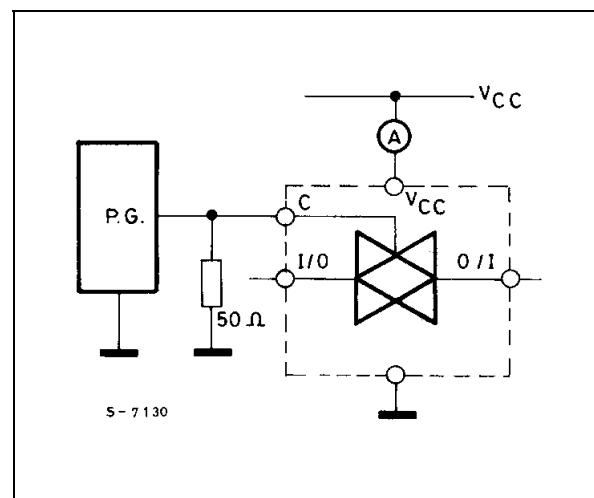
SWITCHING CHARACTERISTICS WAVEFORM



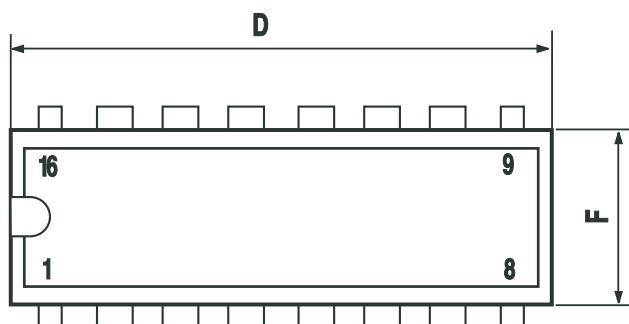
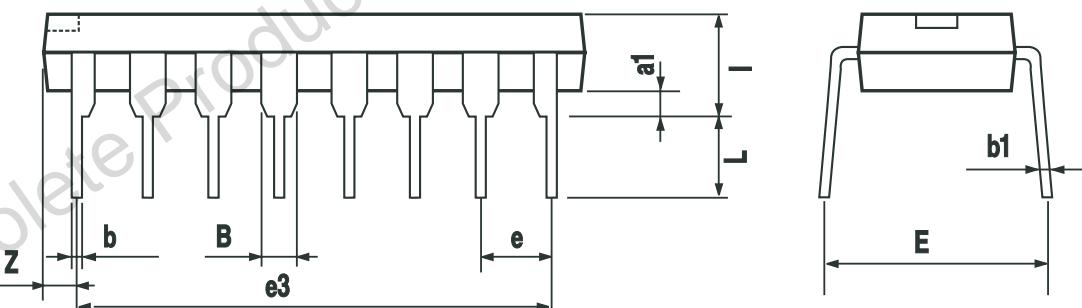
CHANNEL RESISTANCE (R_{ON})



I_{CC} (Opr.)



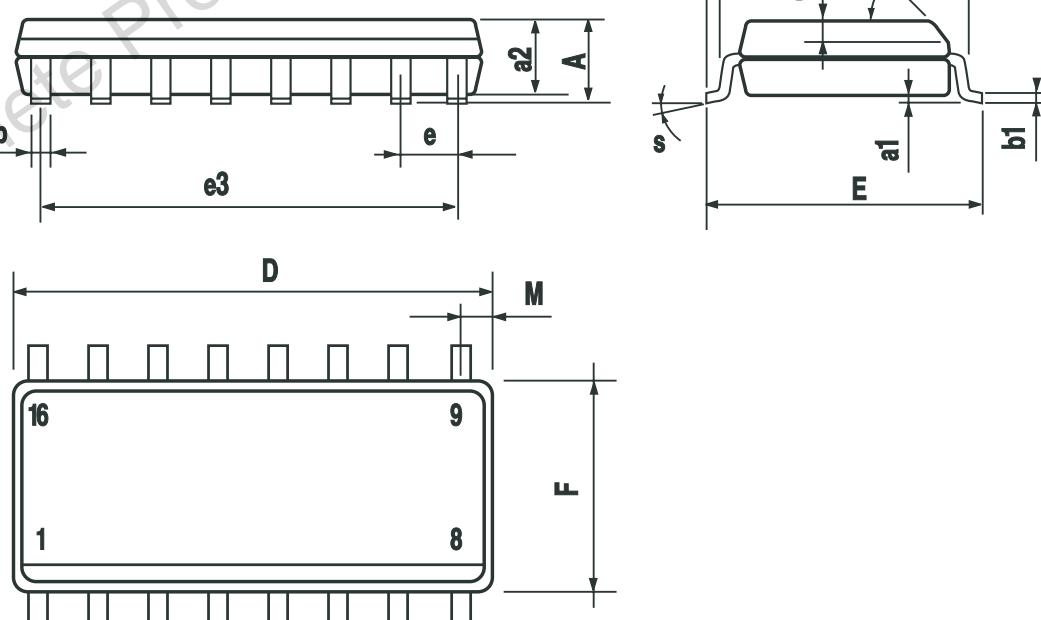
Plastic DIP-16 (0.25) MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

SO-16 MECHANICAL DATA

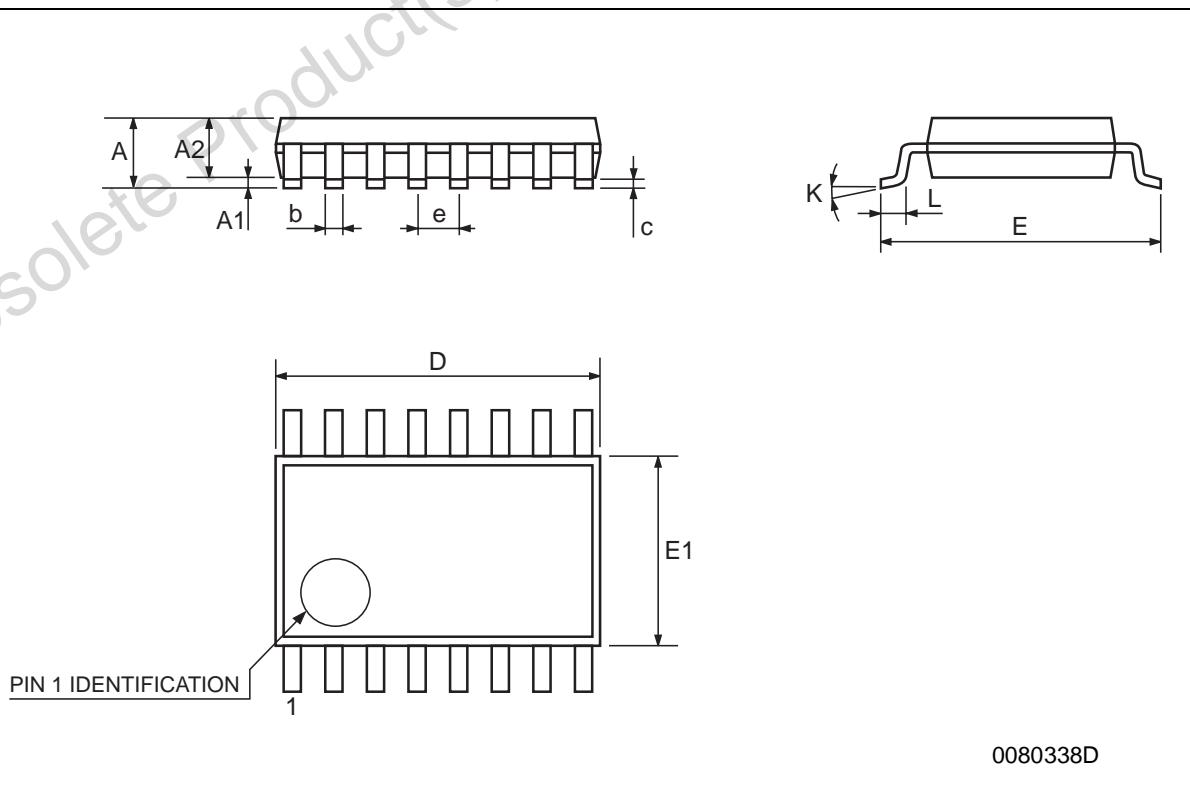
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.008
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1		45° (typ.)				
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8			° (max.)		



PO13H

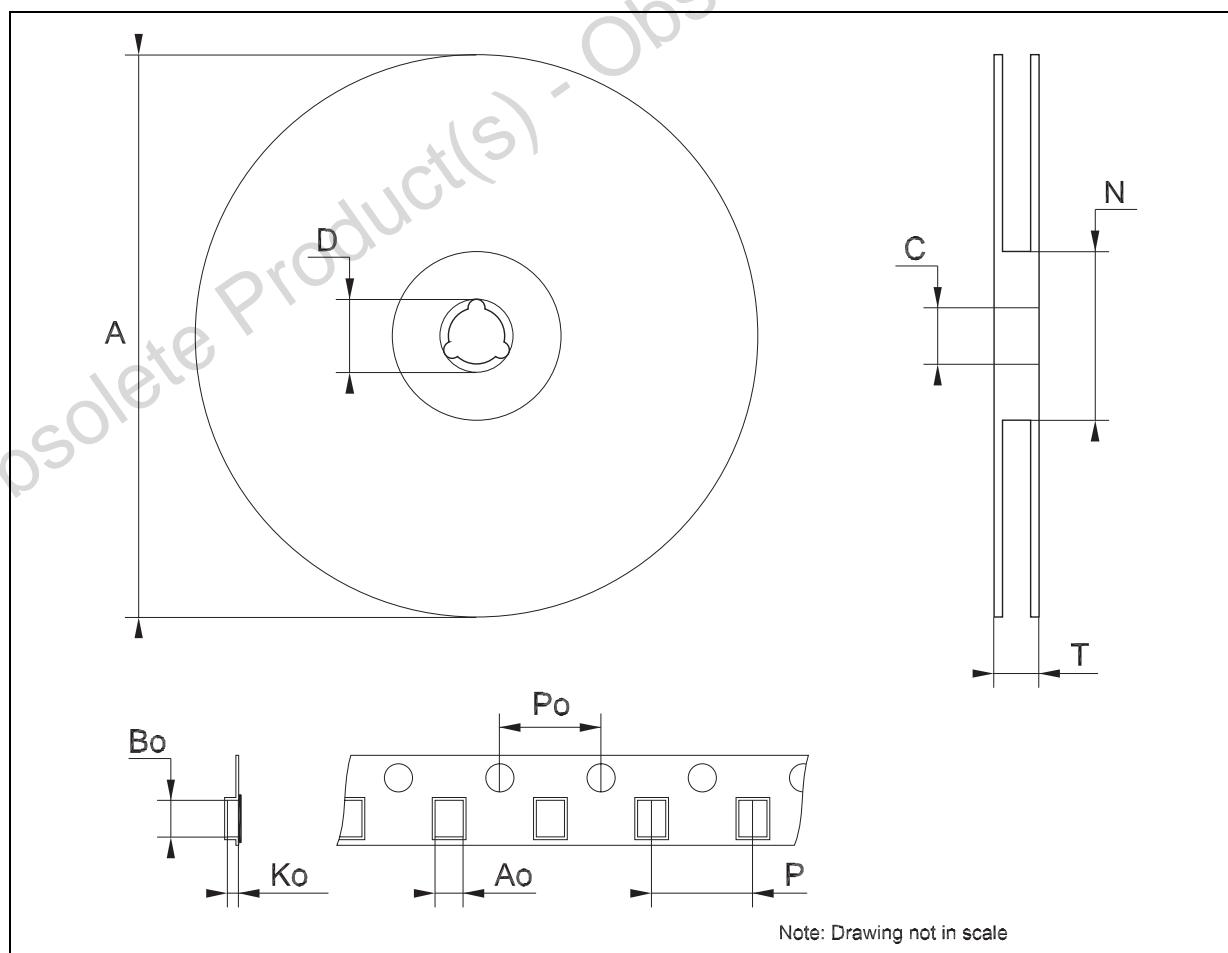
TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



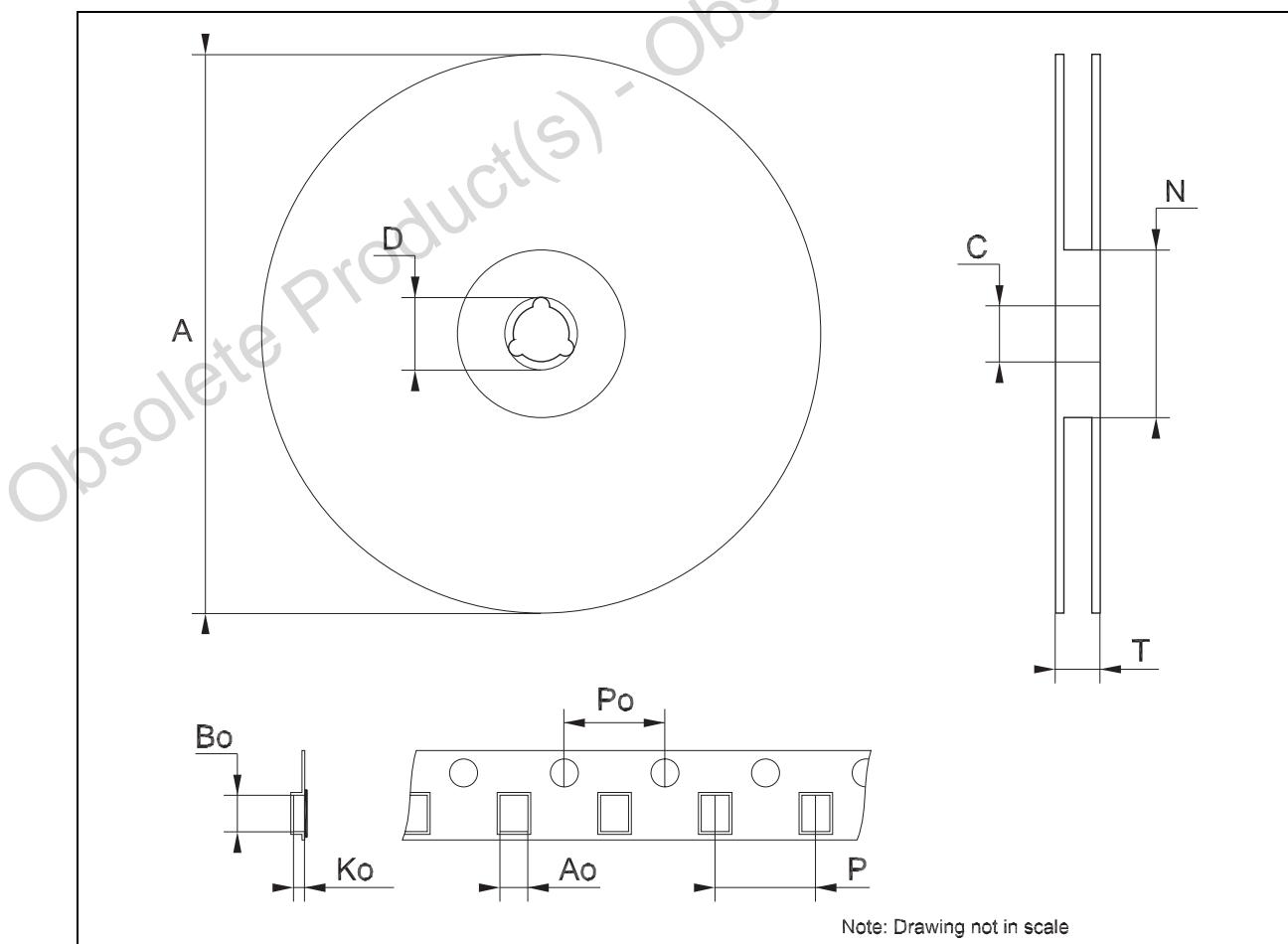
Tape & Reel SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.45		6.65	0.254		0.262
Bo	10.3		10.5	0.406		0.414
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



Tape & Reel TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Bo	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



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